EVAL_800W_ZVS_FB_CFD7

Infineon 800 W DC-DC ZVS full-bridge solution for server and industrial SMPS systems

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Zechner Florian

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General

Description:

› The **"EVAL_800W_ZVS_FB_CFD7"** is a high performance example with a complete Infineon solution. The board includes high voltage and low voltage power MOSFETs, controllers and drivers, demonstrating a very effective way to design the high voltage DC-DC stage of a server or industrial SMPS fulfilling the highest standard of efficiency and reliability. The overall best-in-class performance is achieved because of a mix of proper control techniques and best-in-class power device selection. Key Infineon products used to achieve this performance level include: 600 V CoolMOS™ CFD7 superjunction (SJ) MOSFET (IPA60R280CFD7), advanced EiceDRIVER™ 2EDN dual-channel gate driver (2EDN7524F), OptiMOS™ 5 80 V synchronous rectification MOSFET (BSC026N08NS5), XMC4200 microcontroller (XMC4200-F64K256 AB), CoolSET™ bias converter flyback controller + switch (ICE3RBR4765JZ).

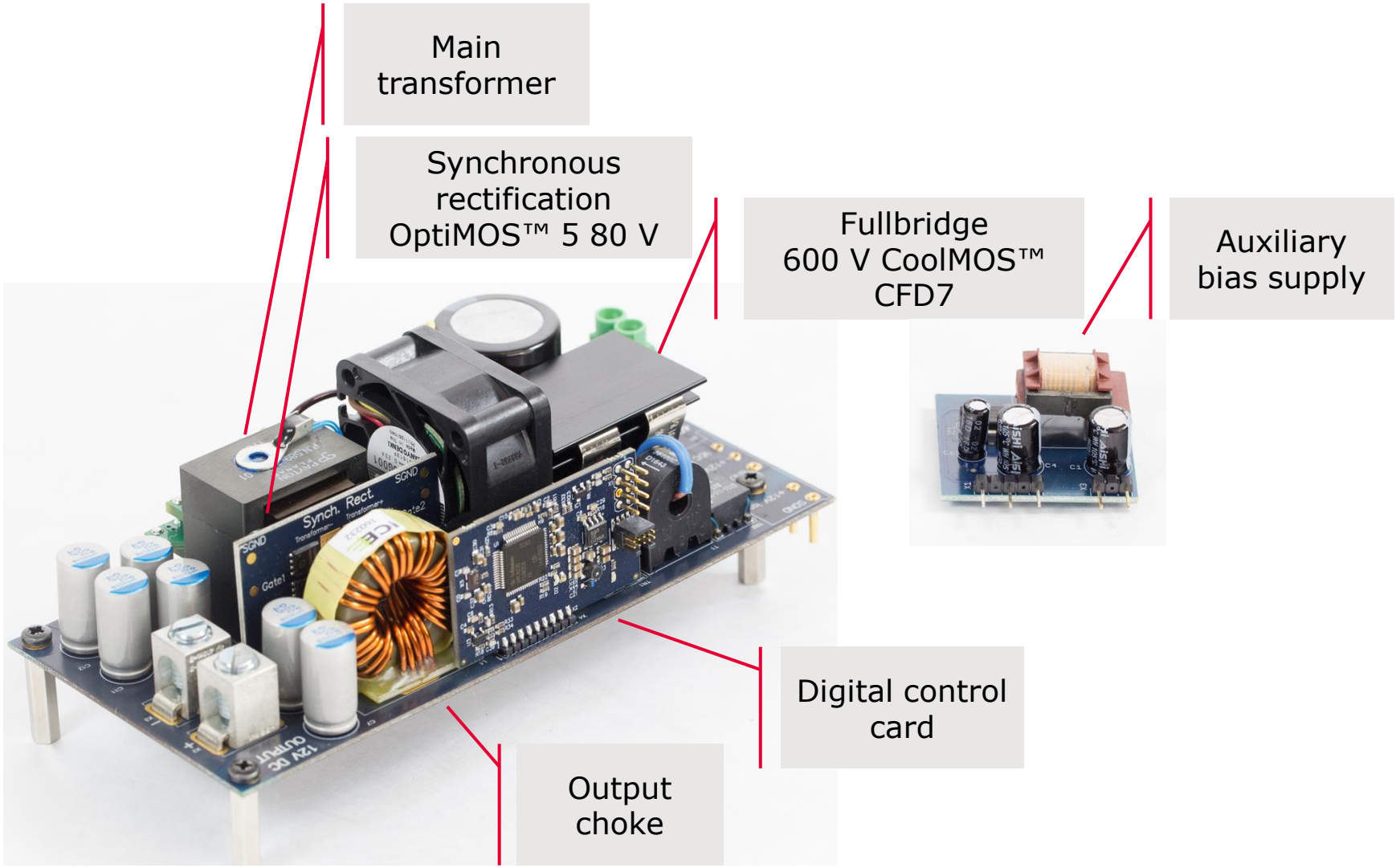
Summary of features:

› Input voltage: 350-410 V_{DC} (nom. 400 V_{DC})
› Output voltage: 12 V ±4%
› Max. output current/power: 67 A/800 W
› Switching frequency: 100 KHz

The following variant is available:

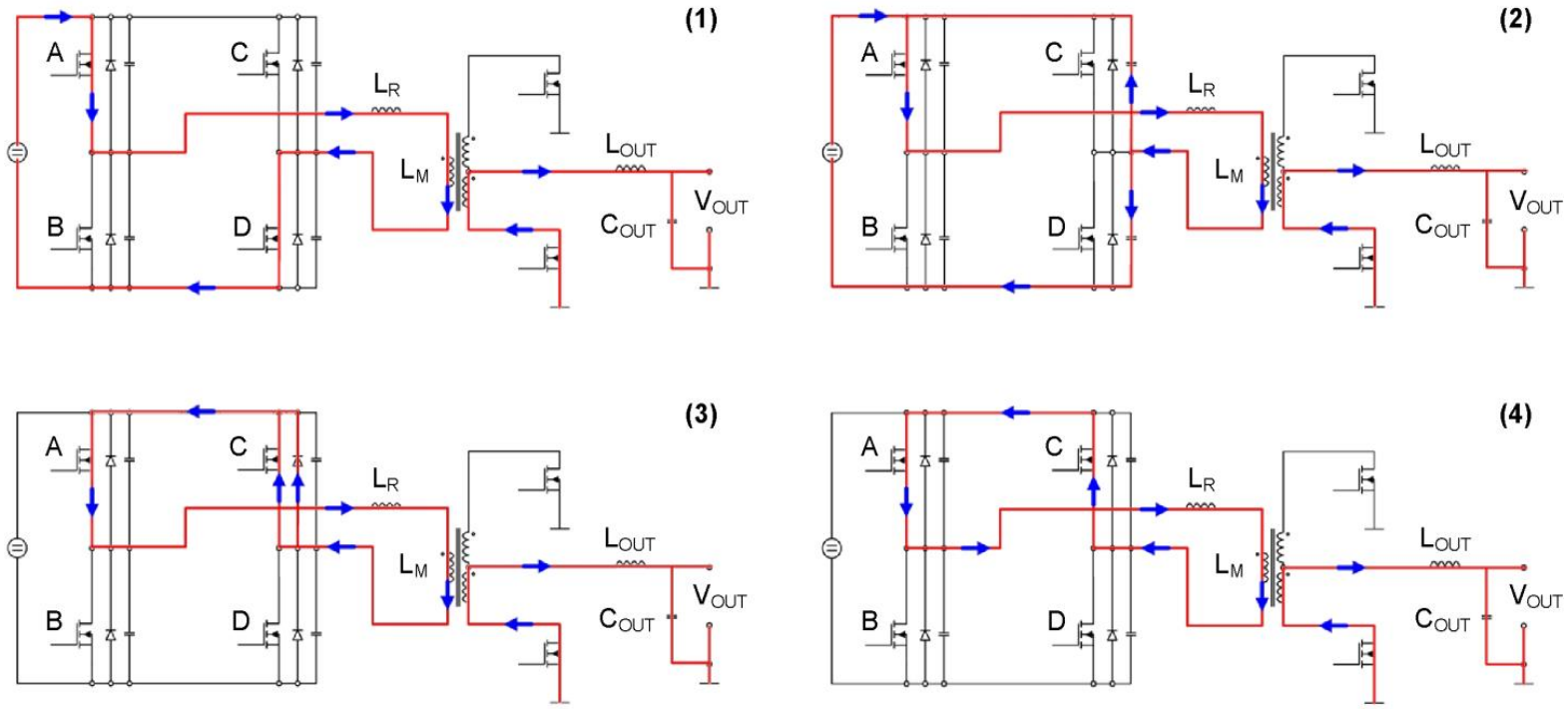
› EVAL_800W_ZVS_FB_CFD7

Infineon 800 W DC-DC ZVS full-bridge solution for server and industrial SMPS systems



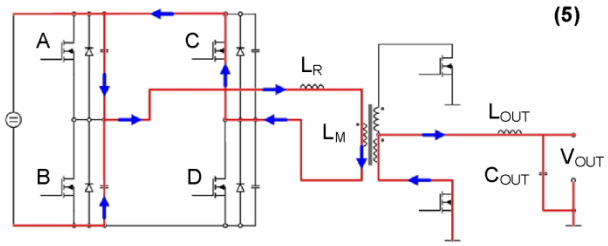
Principle of operation I

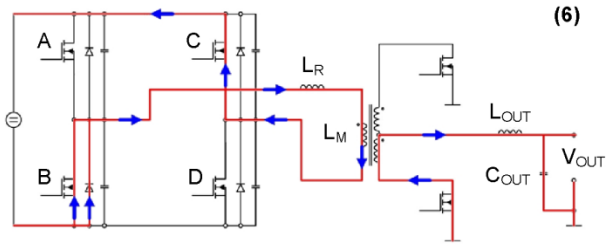
› The ZVS PSFB topology principle of operation is already described in [1]. For the reader's convenience, Figures 2 and 3 recap the fundamental steps

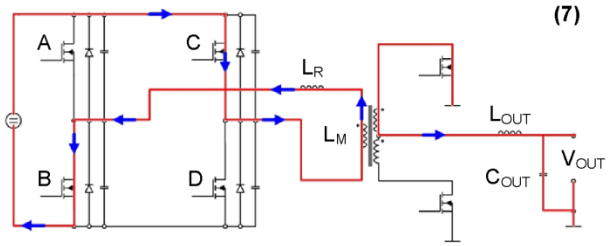


Principle of operation II

- Power transfer phase: MOSFETs A and D are turned on and the current flows as shown in the diagram. During this phase the primary current is rising according to the value of the total primary inductance
- The second phase is responsible for the zero-voltage switching of MOSFET C. In order to reach a zero-voltage turn-on, the energy stored in the resonant inductance is used to discharge the output capacitance of MOSFET C and charge the output capacitance of MOSFET D
- After the output capacitance of MOSFET C is discharged, the current is commutating to the body-diode of MOSFET C
- MOSFET C is actively turned on and the current is flowing through the channel and not through the body-diode anymore. This phase is also called the “freewheeling phase”

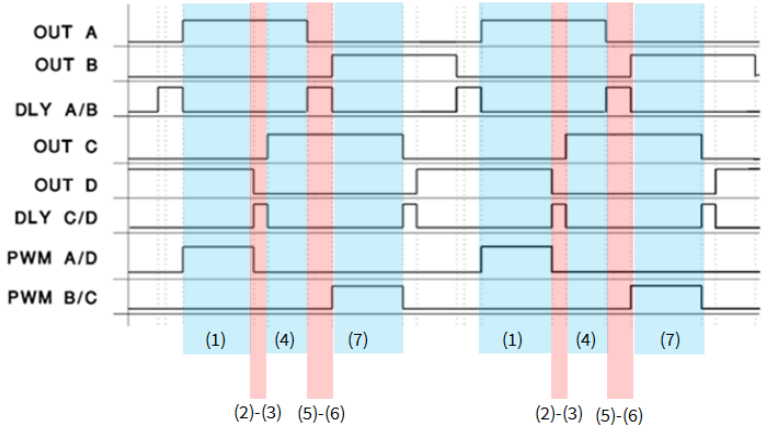






Principle of operation III

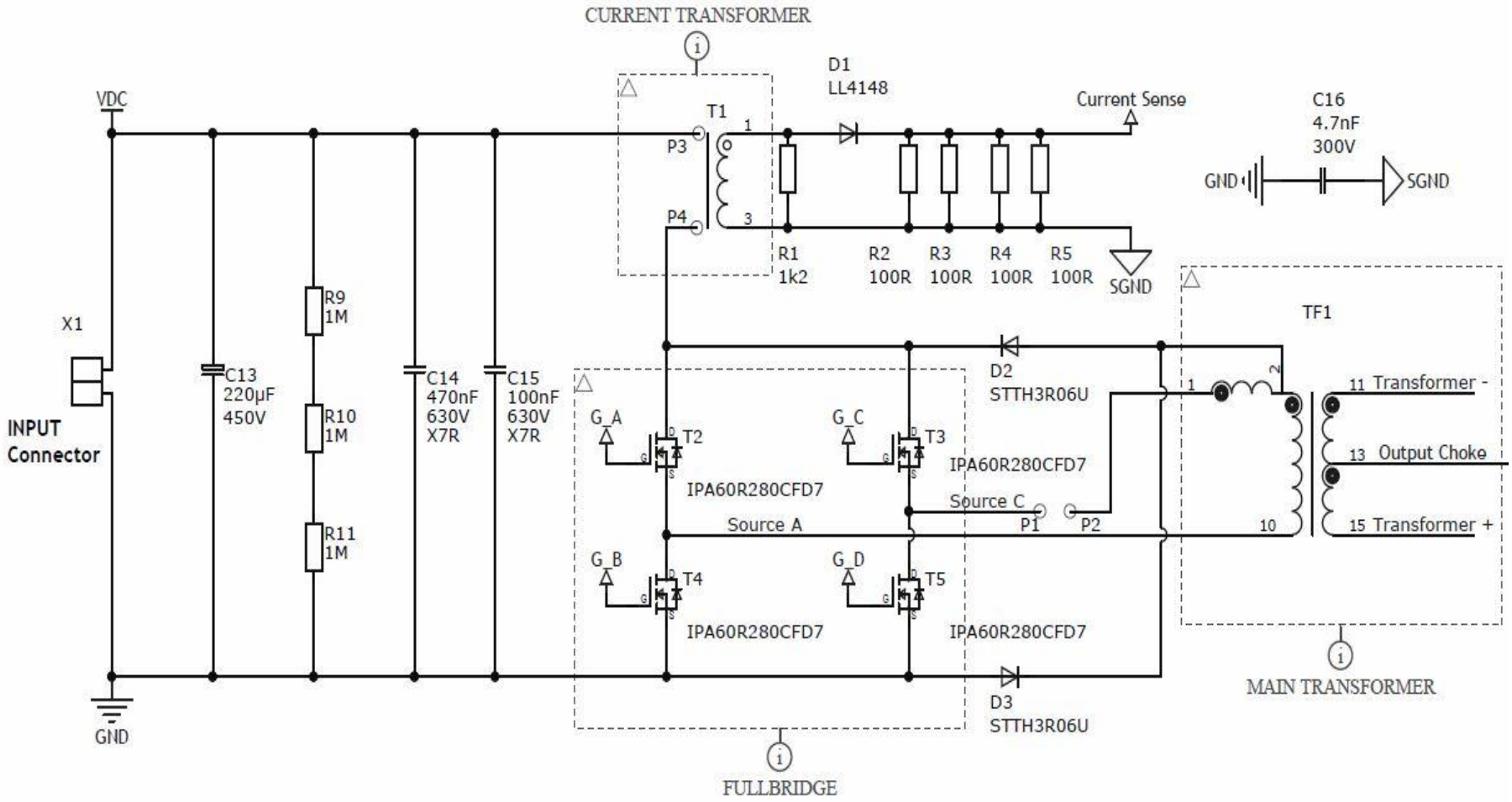
- In order to start a new power transfer phase MOSFET B is turned on. This phase is achieved in the same way as phase 2 by turning off MOSFET A. The output capacitance of MOSFET A is charged and the output capacitance of MOSFET B is discharged before actively switching on the MOSFET
- The body-diode conduction time of MOSFET B, which is visible in this phase, should also be reduced to a minimum as in phase 3
- MOSFET B is actively turned on, the current changes its direction and the next power transfer phase starts
- Figure 4 shows the control signals applied to the four MOSFETs of the bridge
- (1) and (7) are power transfer phases, whose duration defines the total effective on-time (and thus the duty cycle), which is given by the overlapping conducting period of the MOSFET on the same diagonal (A–D and B–C). The time intervals (2)–(3) and (5)–(6) are also called dead times: they represent the time between the turn-off and turn-on of the MOSFETs on the same leg. They must be set long enough in order to achieve the Zero Voltage Switching (ZVS) turn-on



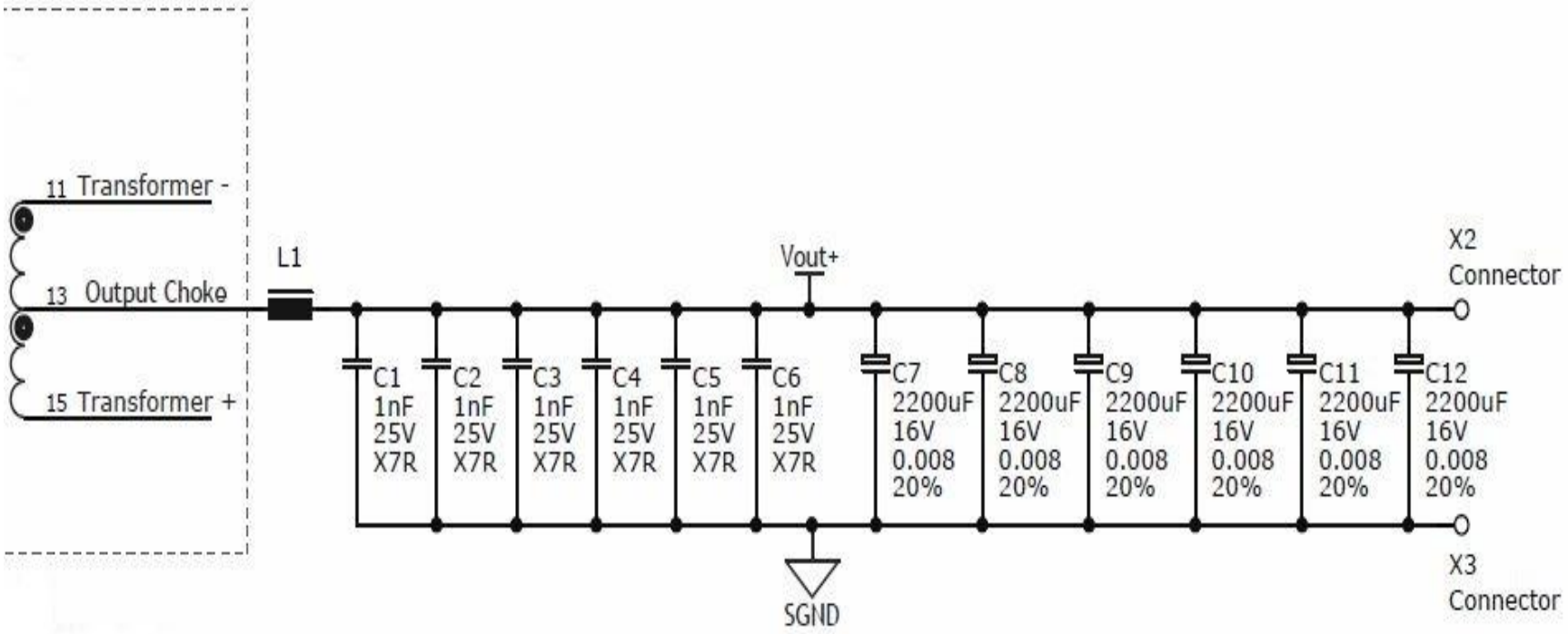
Principle of operation IV

- It can be observed that the duration of these two times is not equal: the one applied to the C–D leg is lower compared to the one applied to the A–B leg. This is because C–D starts a ZVS transition after a power transfer phase, so with more resonant energy available compared to A–B, which starts the transition before the power transfer
- For this reason C–D is commonly called the "lagging leg" and A–B the "leading leg"
- Thus, assuming the same MOSFETs (C_{oss}) are used in the two legs, the time needed to discharge the output capacitance is obviously lower for the lagging leg compared to the leading leg
- Further and more detailed explanations of the ZVS PSFB topology operation and control, including the secondary synchronous rectification, are reported in section 4 of this document

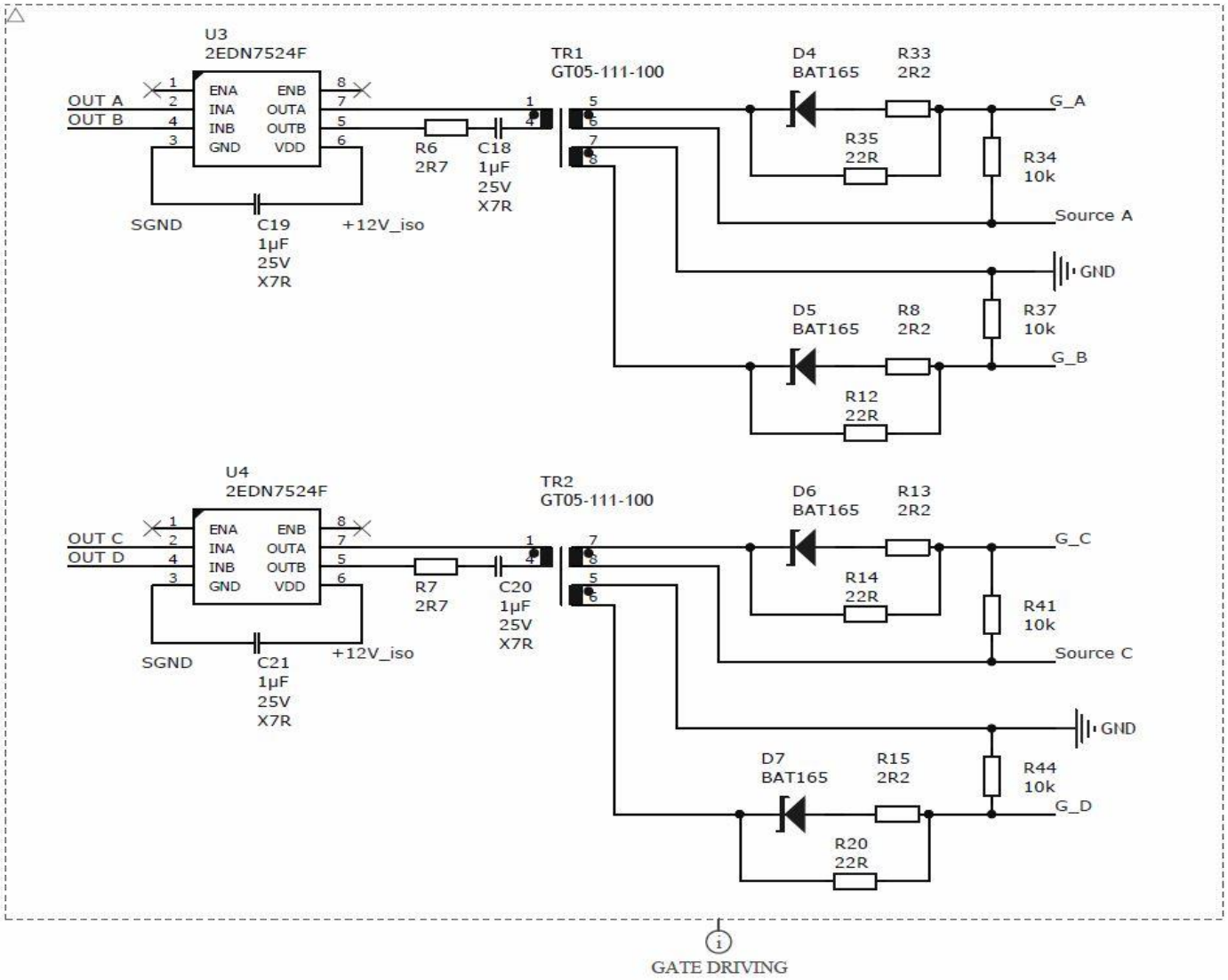
Board schematics
Main converter - primary side



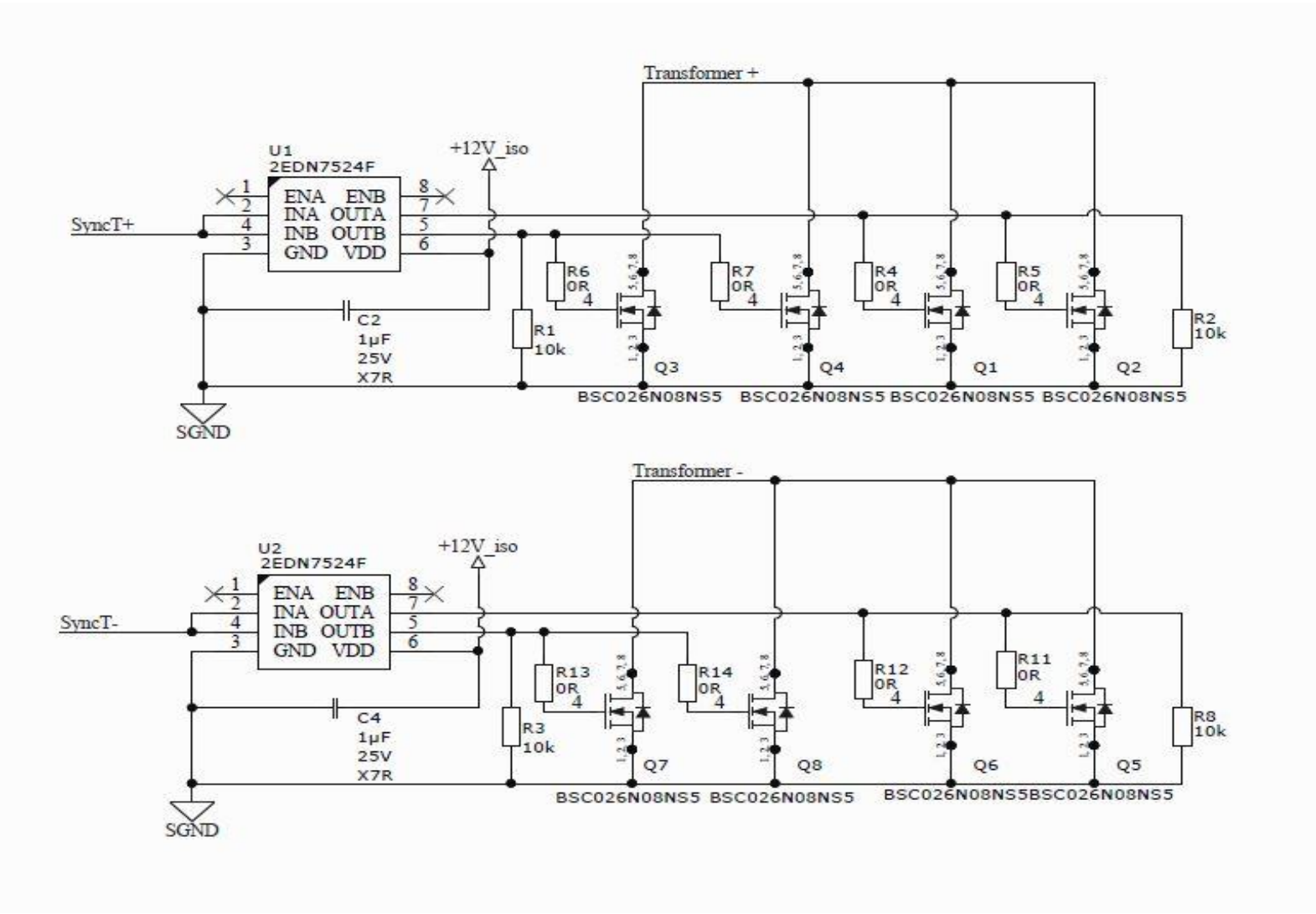
Board schematics
Main converter - secondary side



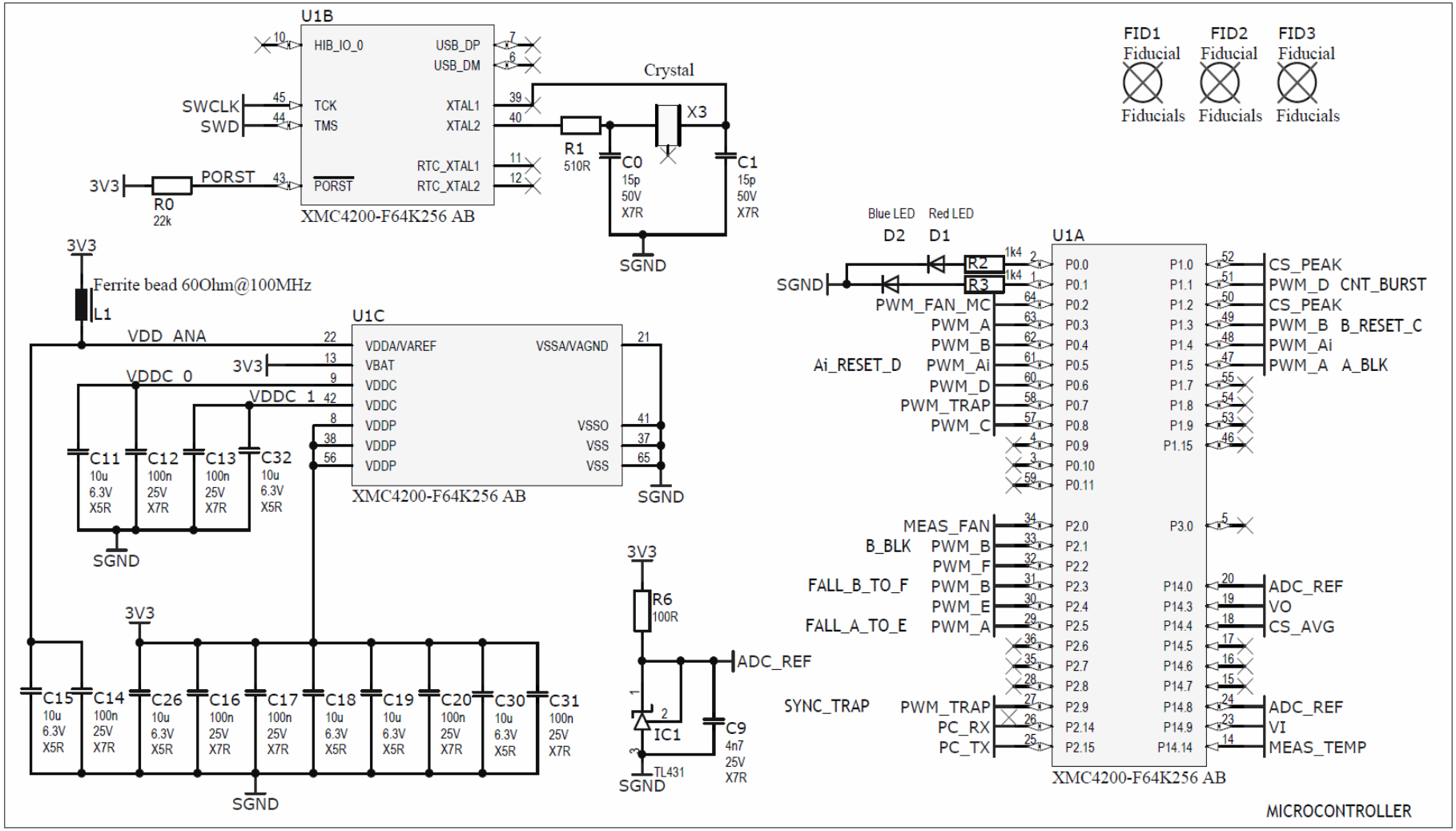
Board schematics
Main converter - gate driver



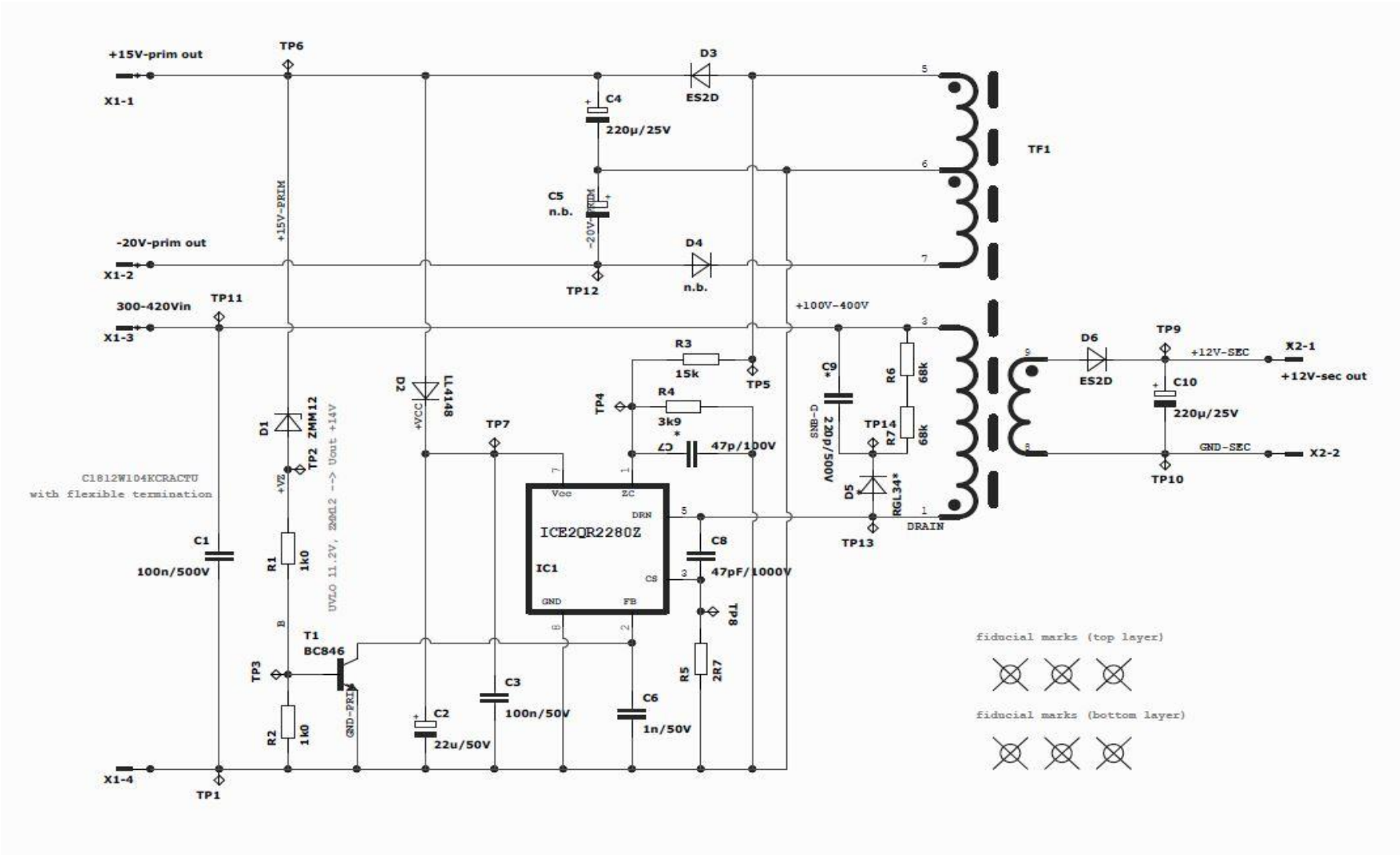
Board schematics
Synchronous rectification daughter card



Board schematics
Control board - microcontroller pin-out



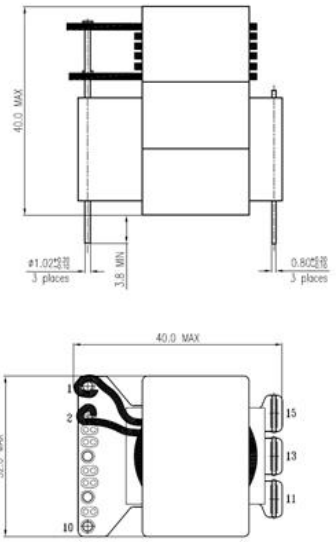
Board schematics
Auxiliary bias supply



Magnetic
Main transformer

Measurement	Terminal	Specification
Magnetizing inductance	2–10	2.1 mH +/- 20% @ 100 kHz, 0.5 V_{rms}
Leakage inductance	2–10 (11–15 shorted)	4.3 µH nominal @ 100 kHz, 0.5 V_{rms}
Inductor inductance	1–2	21 µH +/- 15% @ 100 kHz, 0.5 V_{rms}
DCR	1–10 11–15	280 mΩ max. 0.6 mΩ max.
TR	2–10:11–13 2–10:13–15	22 22
Hi-pot **Hi-pot** **Hi-pot**	Pri. to sec. Pri. to core Sec. to core	4.0 kV AC, 6 mm creepage 2.5 kV AC 0.5 kV DC

Electrical specifications at 25°C ±5°C:

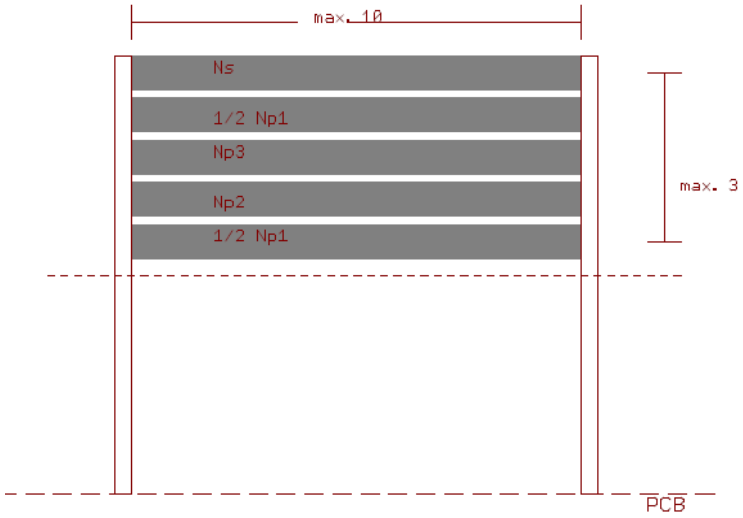


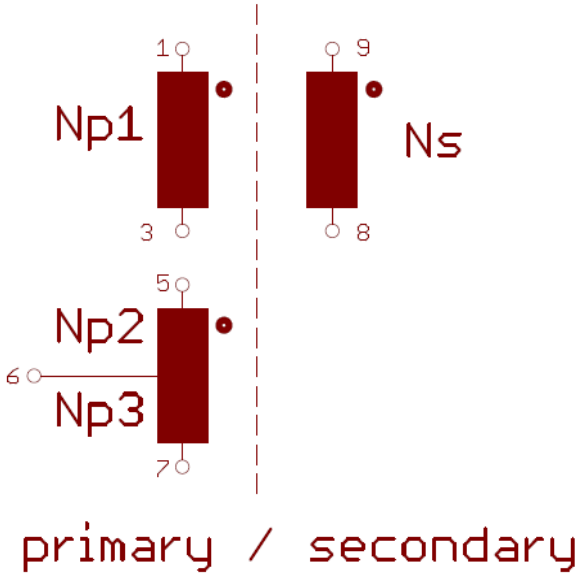
Magnetic
Output choke

800W ZVS Phase Shift Full Bridge Output Choke Design_
F. Di Domenico

Core Part Number:	Magnetics 58930-A2 or CSC CH270125 or equivalent
Permeability:	125
Inductance Factor:	157 mH/1000 Turns
Core Area:	0.661 sq cm
Path Length:	6.54 cm
Turns:	6
Wire Size:	3 strands of #12 AWG or 5 strands diam. 1.25mm
DC Resistance:	0.001 Ohms
Header P/N:	TV-H4916-4A
Wound Core Dimensions:	TDB
Inductance (full load):	2.05 µH
Inductance (no load):	5.65 µH
Core Losses:	811.2 mW
Copper Losses:	4894.0 mW
Total Losses:	5705.2 mW
Temp. Rise:	63.0 degrees C

Magnetic
Bias transformer





Coil build-up:

primary: Np1: 140 Wdg. CuL D=0,15mm --> Lp=4155uH D: Durchmesser
Np2: 20 Wdg. CuL D=0,25mm
Np3: 29 Wdg. CuL D=0,25mm

secondary: Ns: 18 Wdg. CuL D=0,25mm

Coresize/Type: EE16/8/5
Core material: N87 or comparable
Airgap: 0,1mm on center tap (Al=212nH)

Operation frequency: 100kHz
Isolation class: B (130°C)

Withstand voltage:
Np1+Np2+Np3 against Ns 2000V / 50Hz / 2s
Np1 against Np2+Np3 500V / 50Hz / 2s

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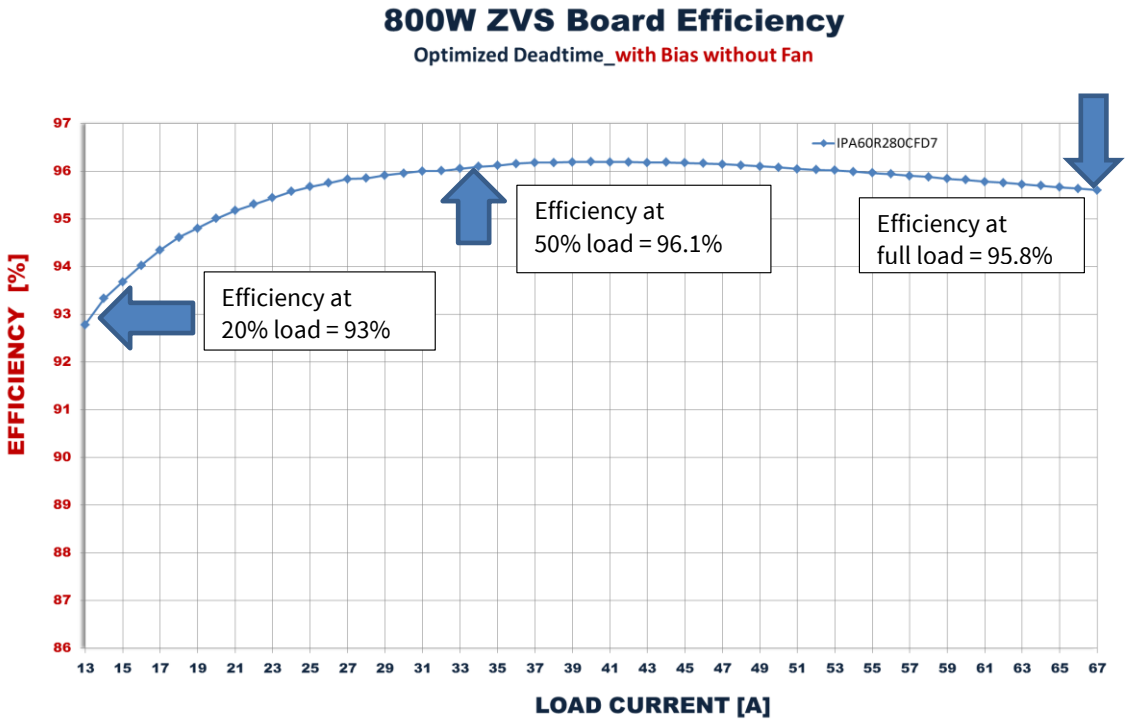
Efficiency plots

- The efficiency plots reported here are measured with a fully automated set-up and following the typical procedures prescribed by the 80+ standard (see [11] for more details)
- The plot shown in Figure 80 has been measured including the BIAS absorption, except the power needed for the fan, which is supposed to be supplied by an external source. Of course the efficiency under light load is strongly influenced by the efficiency of the used auxiliary converter. A further improvement of it is already planned, consisting of the replacement of the BIAS board with a new design, based on the new Infineon CoolSET™ 5 series, as already mentioned in paragraph 3.1.5.1



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Design concept

This general description provides an overview of the Infineon 800 W ZVS PSFB demo board based on the new CoolMOS™ CFD7 technology, for extended information please refer to the related application note.

- The design concept and the performance evaluation are described in the Application Note with special focus on the key contribution of the CoolMOS™ CFD7 technology to enable high efficiency combined with reliable operation across the whole load range, including the typical critical modes of this topology. In fact the demo board design is optimized for the 280 mΩ 600 V CoolMOS™ CFD7 device, namely IPA60R280CFD7.
- An important contribution to the final excellent results also comes out of the applied digital control by Infineon XMC4200. Two possible options, peak current mode and voltage mode, are offered to users for the converter control: these two are in fact the most popular in SMPS application of the PSFB topology. The applied control paths, on both the primary and secondary MOSFETs, with optimized delay time setting, enable an efficiency plot targeting the HV DC-DC stage of a 80+ Platinum level server power supply. A GUI has been designed to help the user interact with the demo board: it enables real-time reading of some key electrical parameters, along with the possibility of designing fine-tuning and protection monitoring.
- The planar main transformer with stacked resonant choke helps achieve the high power density of the demo board and minimizes AC and core losses, resulting in high efficiency across the entire load range, along with a perfect heat spread.
- The final result is a robust and high-performance design able to fulfill all the general requirements for the HV DC-DC isolated stage of a server or industrial SMPS.

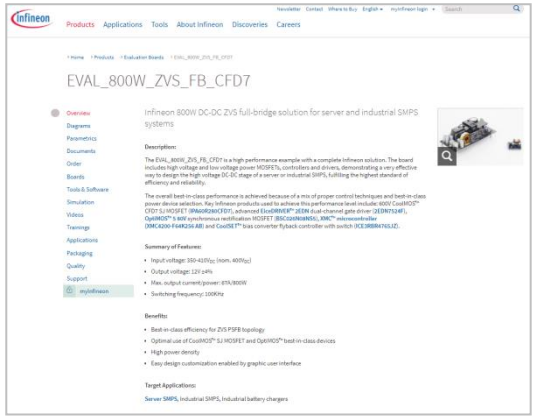
Design concept

- This paper demonstrates that the ZVS PSFB topology is a valuable alternative to the LLC topology in addressing the 80+ Platinum standard. A proper power devices selection, both in the primary and secondary side, and an appropriate control enable a good balance of performance, cost and reliability, avoiding all the pitfalls of a fully resonant approach, as in the LLC topology.
- Further developments of the present design are already planned at Infineon.
- The first derivative is a 1400 W version in the same form factor, which means with almost 80 percent increased power density compared to the 800 W version. 800 W and 1400 W will cover two typical power ranges used today in the server SMPS arena.
- The 800 W ZVS PSFB demo board is also suitable for combining with the 800 W CCM PFC Infineon demo board in order to provide an example of complete server SMPS achieving 80+ Platinum efficiency levels.
- A way to improve the efficiency further, especially under light load conditions, is to replace the BIAS board with a new one based on the latest Infineon CoolSET™ (ICE5QSAG) controller and 800 V CoolMOS™ P7 MOSFET (IPU80R4K5P7).
- Finally, the gate-driving concept used for the HV MOSFETs on the primary side is also going to be improved thanks to the upcoming Infineon 2EDS family of driver ICs with reinforced isolation: this will enable replacement of the gate drive transformers and will provide a reliable and efficient solution with even smaller form factor.

Support slides
EVAL_800W_ZVS_FB_CFD7 design

Evaluation board page

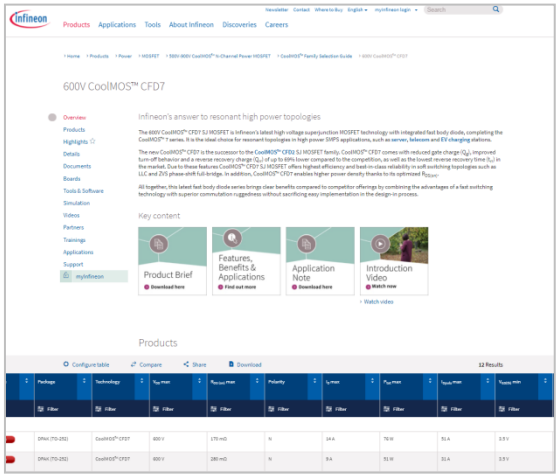
- Technical description
- Datasheets
- Parameters
- Related material
- Videos



- EVAL_800W_ZVS_FB_CFD7

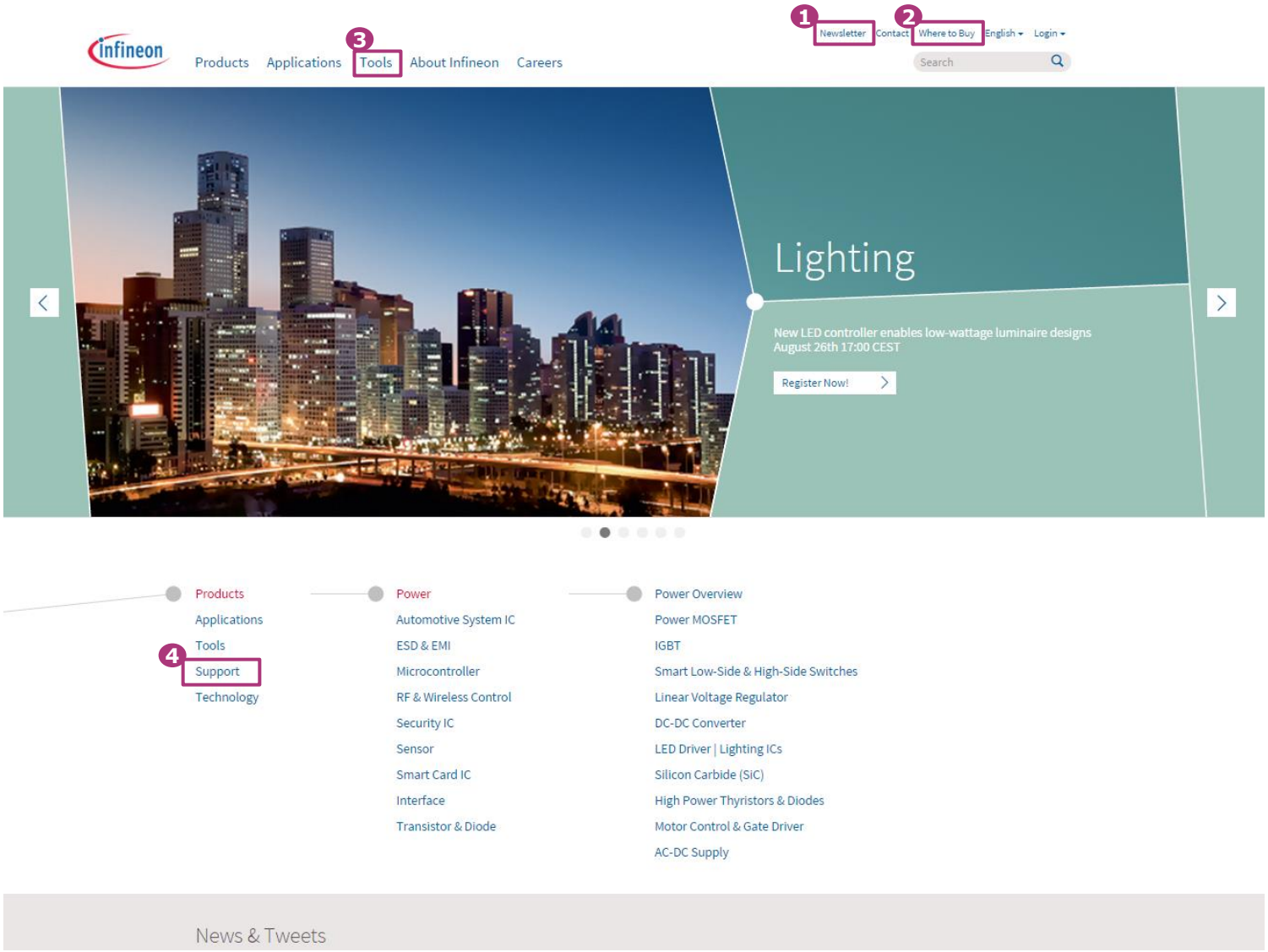
Product family pages

- Product brief
- Application notes
- Selection guides
- Datasheets and portfolio
- Videos
- Simulation models



- IPA60R280CFD7
- BSC026N08NS5
- 2EDN7524F
- XMC4200-F64K256 AB
- ICE3RBR4765JZ

Support
Online tools and services



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